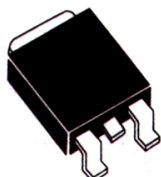




CJD31C NPN  
CJD32C PNP

COMPLEMENTARY SILICON  
POWER TRANSISTOR

DPAK POWER!™



DPAK CASE

**Central**™  
Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CJD31C, CJD32C types are Complementary Silicon Power Transistors manufactured by the epitaxial base process, mounted in a surface mount package designed for power amplifier and high speed switching applications.

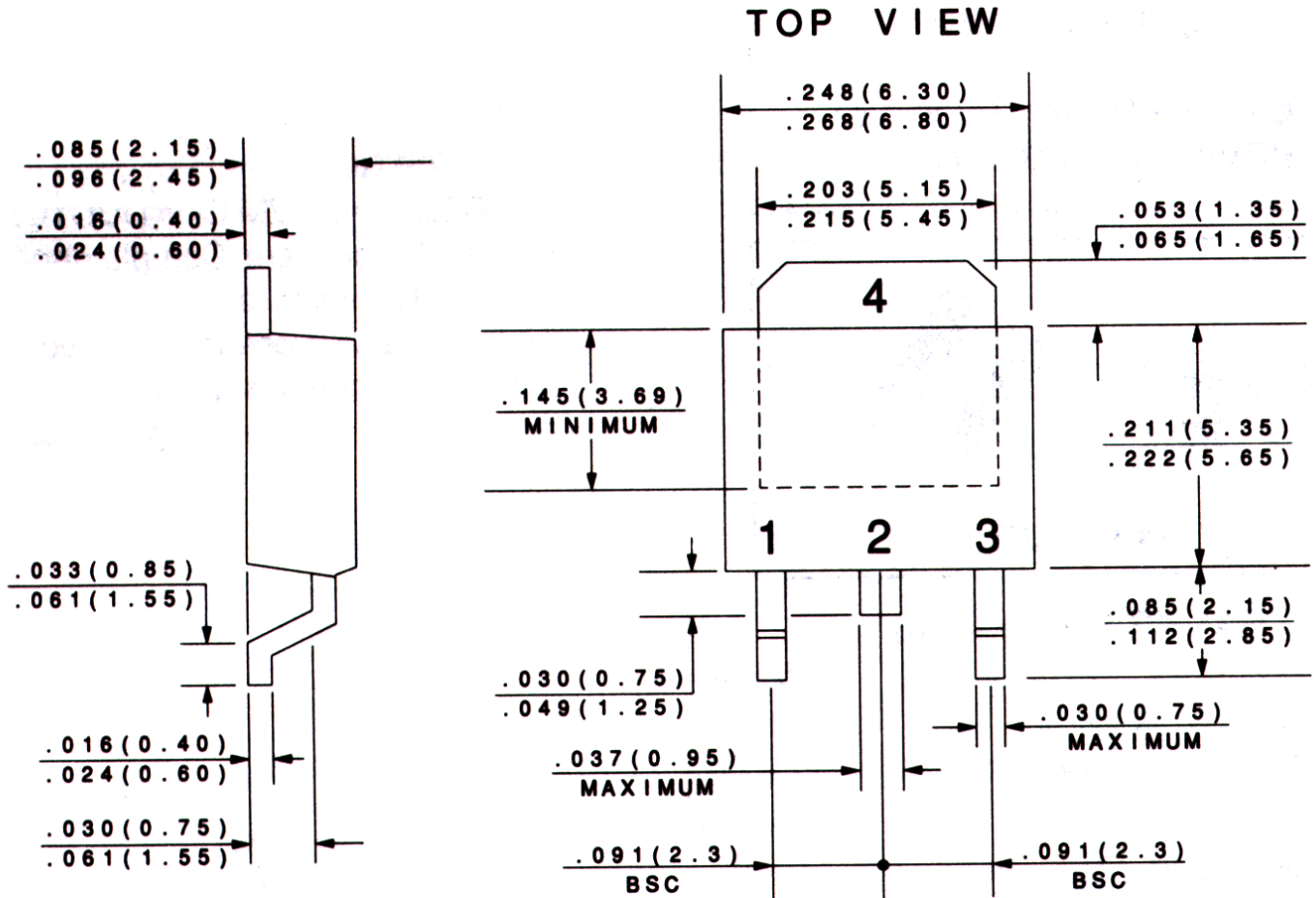
**MAXIMUM RATINGS** ( $T_C=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	100	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Continuous Collector Current	$I_C$	3.0	A
Peak Collector Current	$I_{CM}$	5.0	A
Base Current	$I_B$	1.0	A
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	15	W
Power Dissipation ( $T_A=25^\circ\text{C}$ )	$P_D$	1.56	W
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JC}$	8.33	$^\circ\text{C/W}$
Thermal Resistance	$\theta_{JA}$	80.1	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CEO}$	$V_{CE}=60\text{V}$		50	$\mu\text{A}$
$I_{CES}$	$V_{CE}=100\text{V}$		20	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=5.0\text{V}$		1.0	mA
$BV_{CEO}$	$I_C=30\text{mA}$	100		V
$V_{CE(SAT)}$	$I_C=3.0\text{A}, I_B=375\text{mA}$		1.2	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=3.0\text{A}$		1.8	V
$h_{FE}$	$V_{CE}=4.0\text{V}, I_C=1.0\text{A}$	25		
$h_{FE}$	$V_{CE}=4.0\text{V}, I_C=3.0\text{A}$	10	50	
$f_T$	$V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{MHz}$	3.0		MHz
$h_{fe}$	$V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{kHz}$	20		

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR